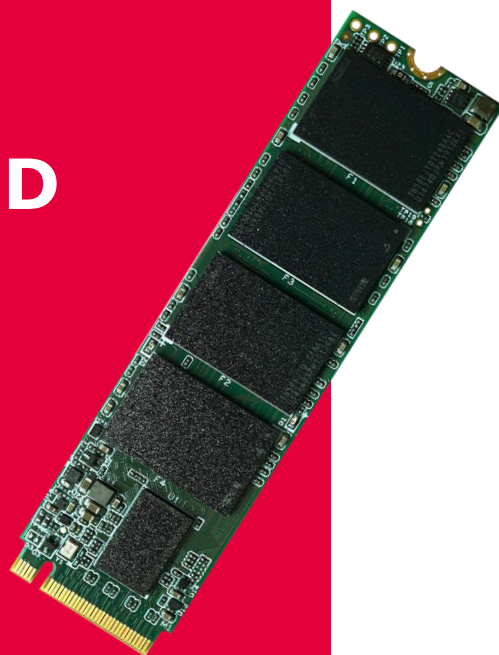


Datasheet

# M.2 (P80) 3TE6 series With Innodisk NAND

- PCIe Gen. III x4, NVMe 1.3
- DRAM-less Solution
- Less Controller Heat
- Anti-Vibration mechanical design
- Hybrid Write Mode
- LDPC ECC engine supported.
- iPowerGuard Protection



## Introduction

Innodisk M.2 (P80) 3TE6 is a NVM Express DRAM-less SSD designed with PCIe interface and industrial 3D TLC NAND Flash. M.2 (P80) 3TE6 supports PCIe Gen III x 4 and it is compliant with NVM 1.3 providing excellent top and also outstanding sustained performance. With sophisticated error detection and correction (ECC) functions, the module can ensure full End-to-End data path protection that secures the data transmission between host system and NAND Flash. In addition, with customized embedded AES-256 bit engine, your data can be further secured.

# M.2 (P80)

## 3TE6 series

Contact us for more information about the M2 (P80) 3TE6.

Innodisk is a service-driven provider of industrial embedded flash and DRAM storage products and technologies, with a focus on the cloud computing, industrial/embedded, and aerospace and defense industries.

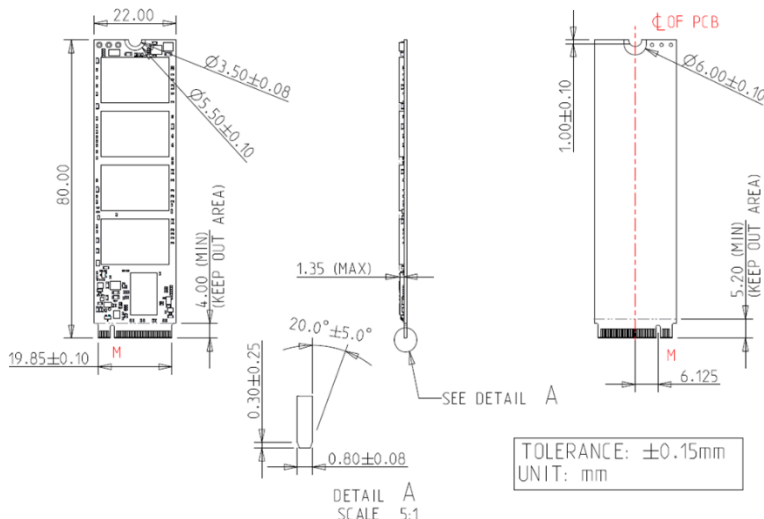
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|  |   |
|--|---|
| Interface                              | PCIe Gen. III x4  |
| Flash Type                             | 3D TLC  |
| P/E cycle                              | 3,000   |
| Capacity                               | 128GB~1TB   |
| Max. Channels                          | 4   |
| Sequential R/W (MB/s, Max)             | 2,050/1,900   |
| Sustained Sequential Write (MB/s, Max) | 900   |
| Max. Power Consumption (RMS)           | 3.6W  |
| Thermal Sensor                         | √   |
| External DRAM buffer                   | NA  |
| H/W Write Protect                      | NA  |
| iCell                                  | NA  |
| Dimension (WxLxH)                      | 22.0 X 80.0 X 1.35 mm   |
| Environment                            | Vibration: 20G @7~2000Hz<br>Shock: 1500G @ 0.5ms<br>Working Temperature: -40°C ~ +85°C<br>MTBF: 3 million hours |

### Ordering Information

| Operation Temp.                 | 128GB             | 256GB             | 512GB             | 1TB               |
|---------------------------------|-------------------|-------------------|-------------------|-------------------|
| Standard Grade<br>(0°C ~ +70°C) | DEM28-A28DD1KCADL | DEM28-B56DD1KCA&L | DEM28-C12DD1KCAQL | DEM28-01TDD1KCAQL |

&. D=2 channel; Q=4 channel